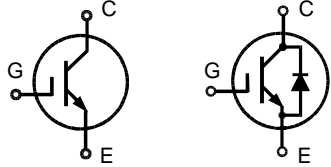


High Voltage IGBT with optional Diode

Short Circuit SOA Capability
Square RBSOA

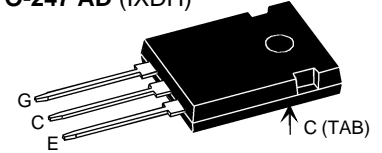
IXDH 30N120
IXDH 30N120 D1
IXDT 30N120
IXDT 30N120 D1

$V_{CES} = 1200\text{ V}$
 $I_{C25} = 60\text{ A}$
 $V_{CE(sat) typ} = 2.4\text{ V}$

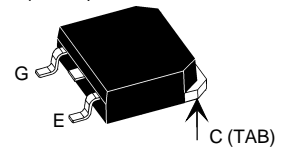


IXDH 30N120 IXDH 30N120 D1
IXDT 30N120 IXDT 30N120 D1

TO-247 AD (IXDH)



TO-268 AA (IXDT)



G = Gate, E = Emitter
C = Collector, TAB = Collector

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1200	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 20\text{ k}\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	60	A
I_{C90}	$T_C = 90^\circ\text{C}$	38	A
I_{CM}	$T_C = 90^\circ\text{C}, t_p = 1\text{ ms}$	76	A
RBSOA	$V_{GE} = \pm 15\text{ V}, T_J = 125^\circ\text{C}, R_G = 47\ \Omega$ Clamped inductive load, $L = 30\ \mu\text{H}$	$I_{CM} = 50$ $V_{CEK} < V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = \pm 15\text{ V}, V_{CE} = V_{CES}, T_J = 125^\circ\text{C}$ $R_G = 47\ \Omega$, non repetitive	10	μs
P_c	$T_C = 25^\circ\text{C}$	IGBT	300 W
		Diode	135 W
T_J		-55 ... +150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
	Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque	1.1/10	Nm/lb.in.
Weight		6	g

Features

- NPT IGBT technology
- low saturation voltage
- low switching losses
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- optional ultra fast diode
- International standard packages

Advantages

- Space savings
- High power density
- IXDT:
surface mountable high power package

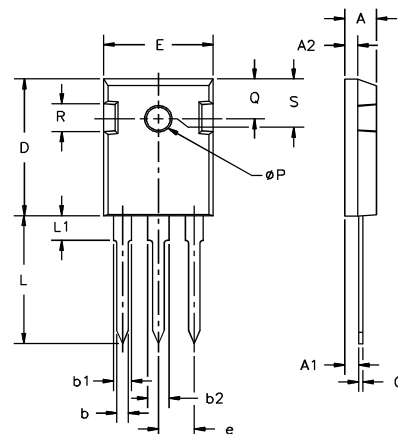
Typical Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{(BR)CES}$	$V_{GE} = 0\text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 1\text{ mA}, V_{CE} = V_{GE}$	4.5		V
I_{CES}	$V_{CE} = V_{CES}$	$T_J = 25^\circ\text{C}$		1.5 mA
		$T_J = 125^\circ\text{C}$	2.5	mA
I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$			$\pm 500\text{ nA}$
$V_{CE(sat)}$	$I_C = 30\text{ A}, V_{GE} = 15\text{ V}$	2.4	2.9	V

Symbol	Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
C _{ies}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		1650	pF
C _{oes}			250	pF
C _{res}			110	pF
Q _g	I _C = 30 A, V _{GE} = 15 V, V _{CE} = 0.5 V _{CES}		120	nC
t _{d(on)}	Inductive load, T _J = 125°C I _C = 30 A, V _{GE} = ±15 V, V _{CE} = 600 V, R _G = 47 Ω		100	ns
t _r			70	ns
t _{d(off)}			500	ns
t _f			70	ns
E _{on}			4.6	mJ
E _{off}		3.4	mJ	
R _{thJC}				0.42 K/W
R _{thCK}	Package with heatsink compound		0.25	K/W

TO-247 AD Outline

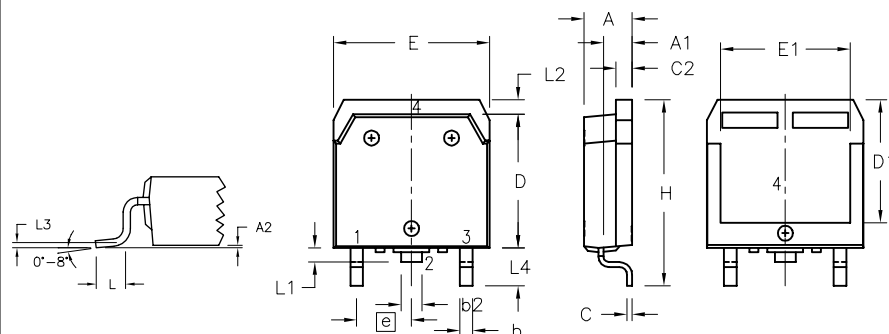


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

Reverse Diode (FRED) [D1 version only]

Symbol	Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
V _F	I _F = 30 A, V _{GE} = 0 V I _F = 30 A, V _{GE} = 0 V, T _J = 125°C	2.5	2.7	V
I _F	T _C = 25°C T _C = 90°C		60	A
I _{RM}	I _F = 30 A, -di _F /dt = 400 A/μs, V _R = 600 V		20	A
t _{rr}	V _{GE} = 0 V, T _J = 125°C		200	ns
t _{rr}	I _F = 1 A, -di _F /dt = 100 A/μs, V _R = 30 V, V _{GE} = 0 V		40	ns
R _{thJC}				1 K/W

TO-268 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.9	5.1	.193	.201
A ₁	2.7	2.9	.106	.114
A ₂	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b ₂	1.9	2.1	.075	.083
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E ₁	13.3	13.6	.524	.535
e	5.45	BSC	.215	BSC
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3		0.25	BSC	.010
L4	3.80	4.10	.150	.161

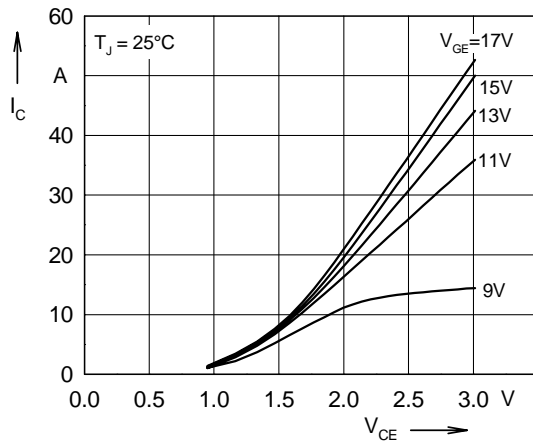


Fig. 1 Typ. output characteristics

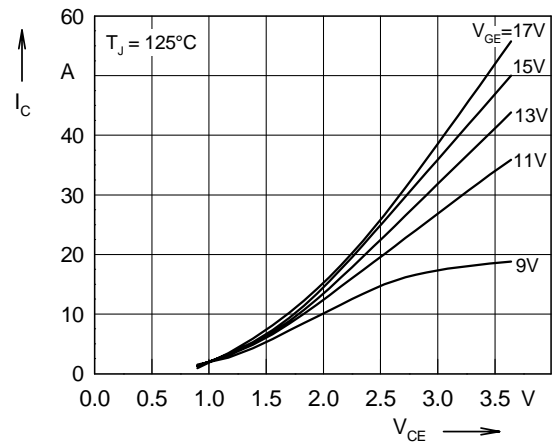


Fig. 2 Typ. output characteristics

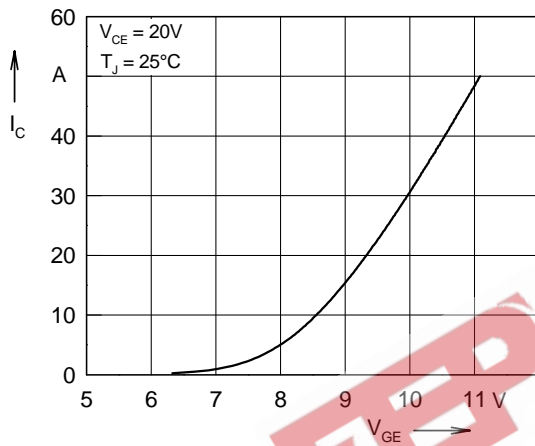


Fig. 3 Typ. transfer characteristics

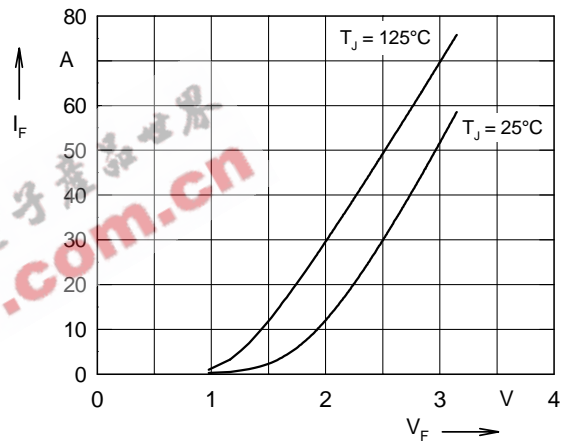


Fig. 4 Typ. forward characteristics of free wheeling diode

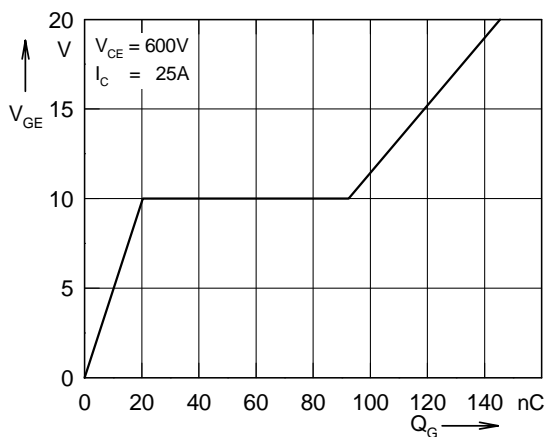


Fig. 5 Typ. turn on gate charge

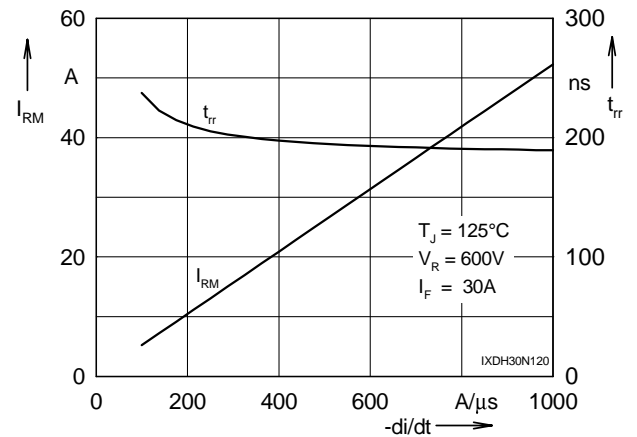


Fig. 6 Typ. turn off characteristics of free wheeling diode

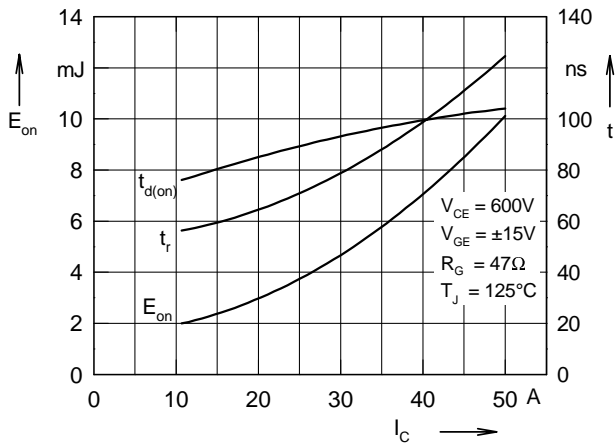


Fig. 7 Typ. turn on energy and switching times versus collector current

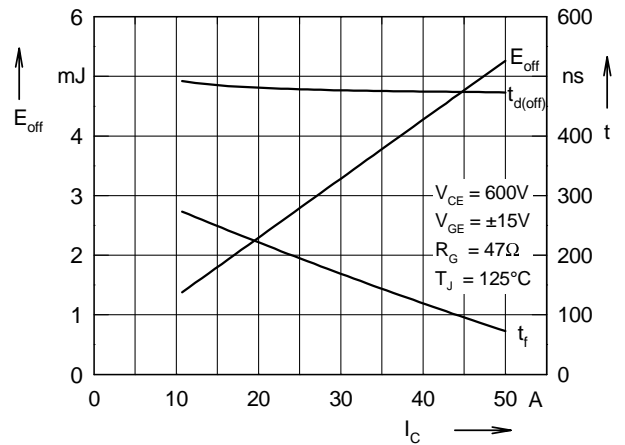


Fig. 8 Typ. turn off energy and switching times versus collector current

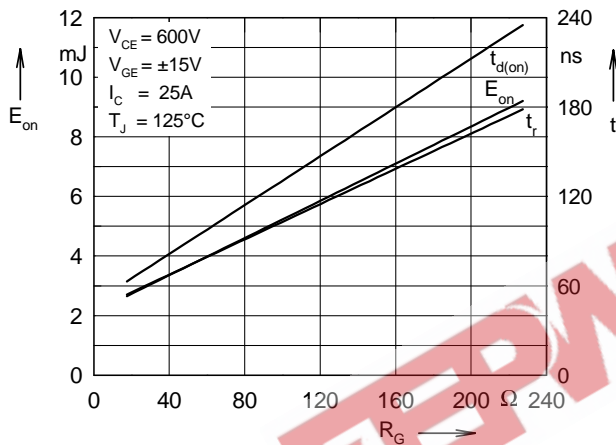


Fig. 9 Typ. turn on energy and switching times versus gate resistor

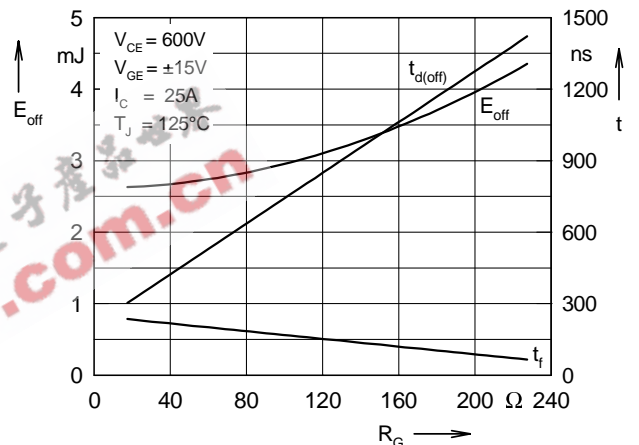


Fig.10 Typ. turn off energy and switching times versus gate resistor

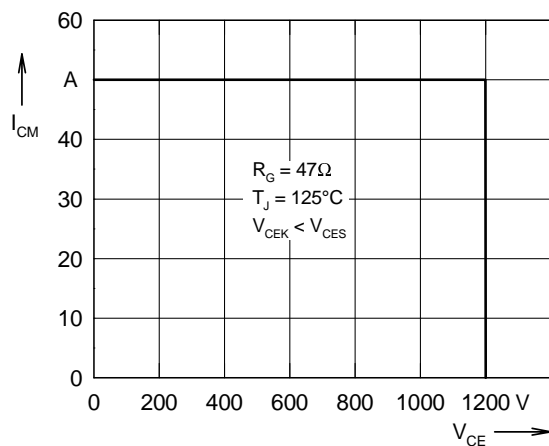


Fig. 11 Reverse biased safe operating area RBSOA

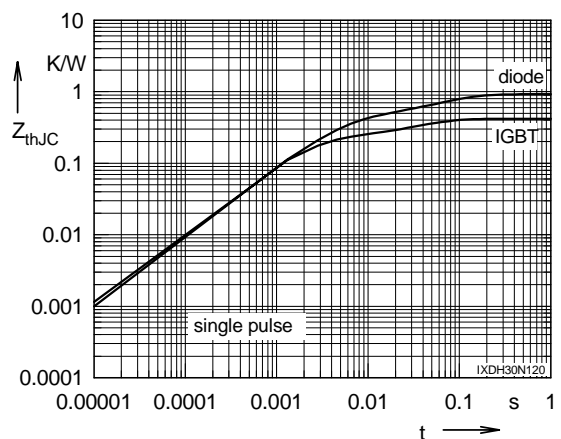


Fig. 12 Typ. transient thermal impedance